



Dual N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

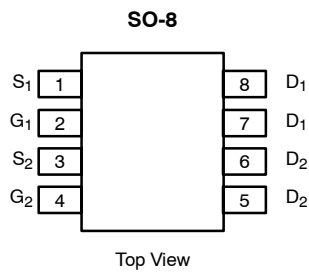
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.0095 @ $V_{GS} = 10$ V	12.2
	0.016 @ $V_{GS} = 4.5$ V	9.4

FEATURES

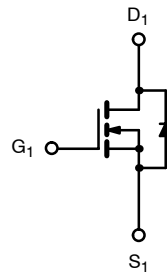
- TrenchFET® Power MOSFET
- 100% R_g Tested

APPLICATIONS

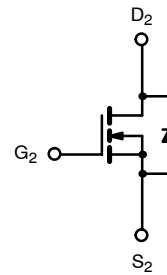
- DC/DC Conversion
- Load Switching



Ordering Information: Si4944DY
Si4944DY-T1 (with Tape and Reel)



N-Channel MOSFET



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V _{DS}	30		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150°C) ^a	T _A = 25 °C	I _D	12.2	9.3	A
	T _A = 85 °C		8.8	6.7	
Pulsed Drain Current		I _{DM}	30		
Continuous Source Current (Diode Conduction) ^a		I _S	1.9	1.1	
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	2.3	1.3	W
	T _A = 85 °C		1.2	0.7	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	42	55	$^\circ\text{C/W}$
	Steady State		75	95	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	19	25	

Notes

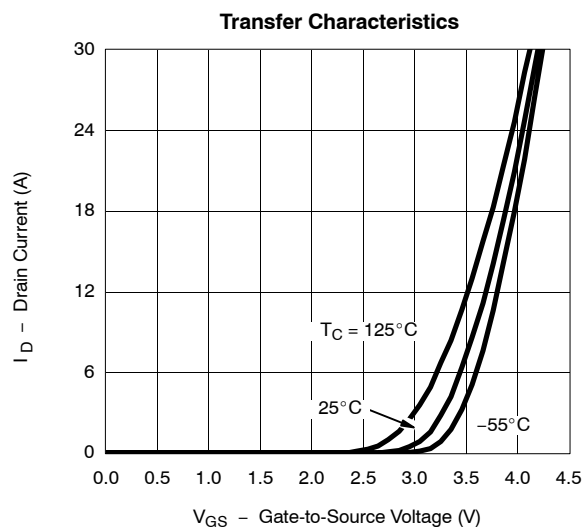
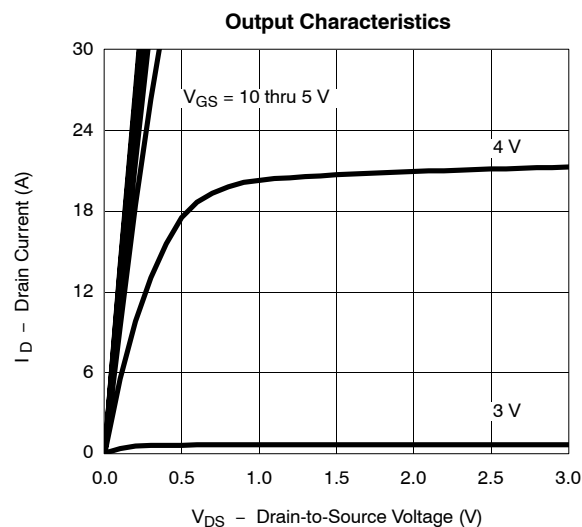
a. Surface Mounted on 1" x 1" FR4 Board.

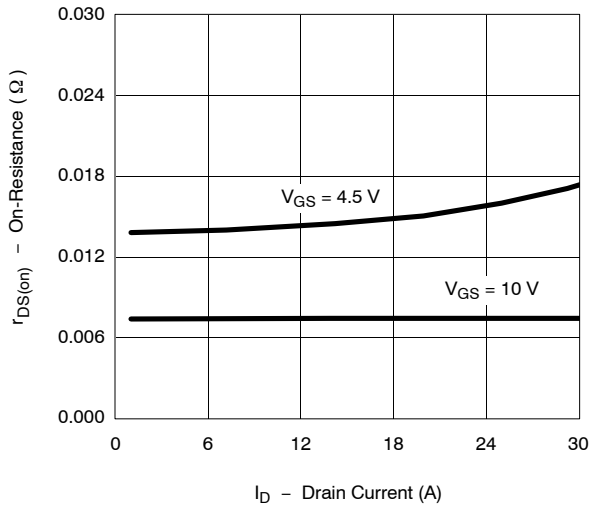
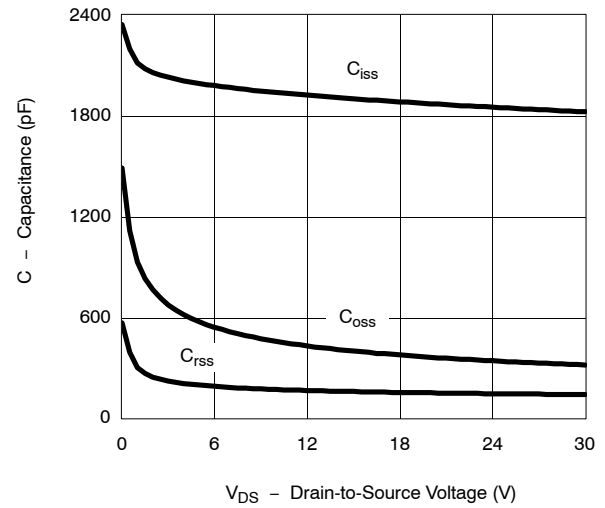
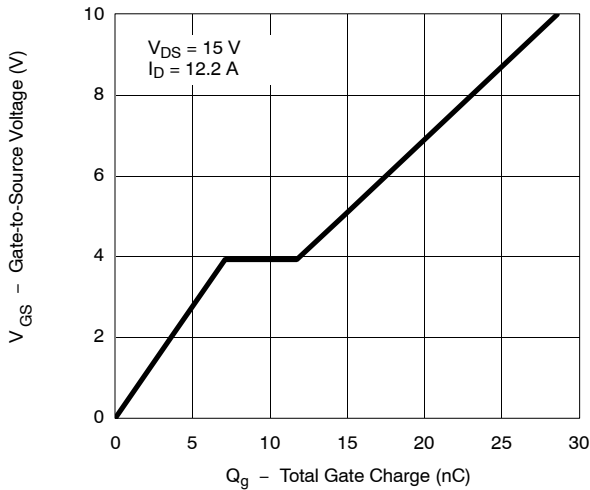
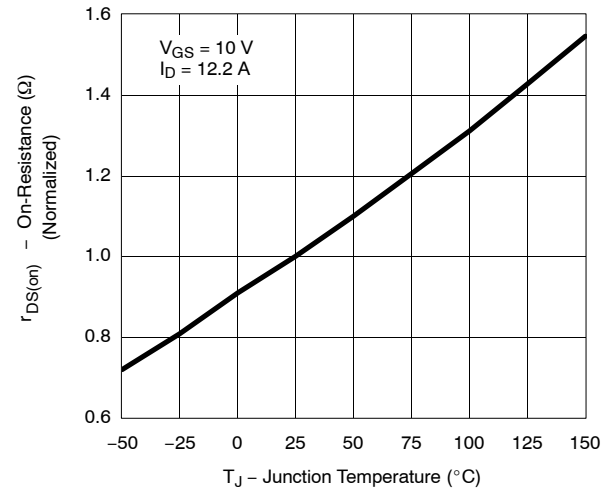
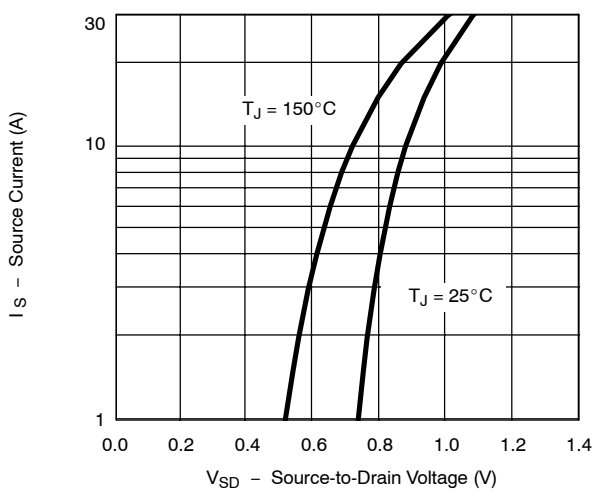
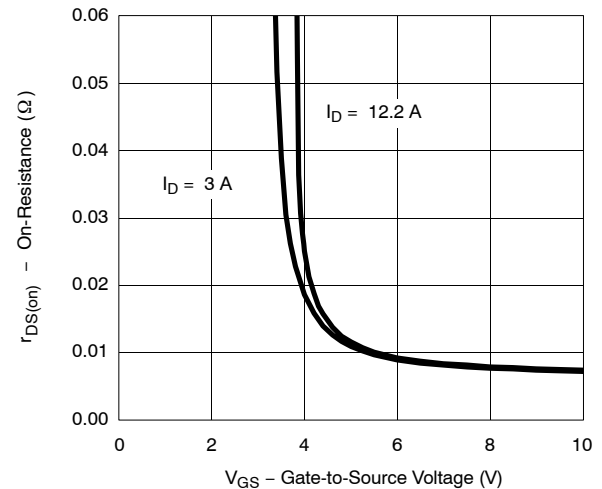
MOSFET SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

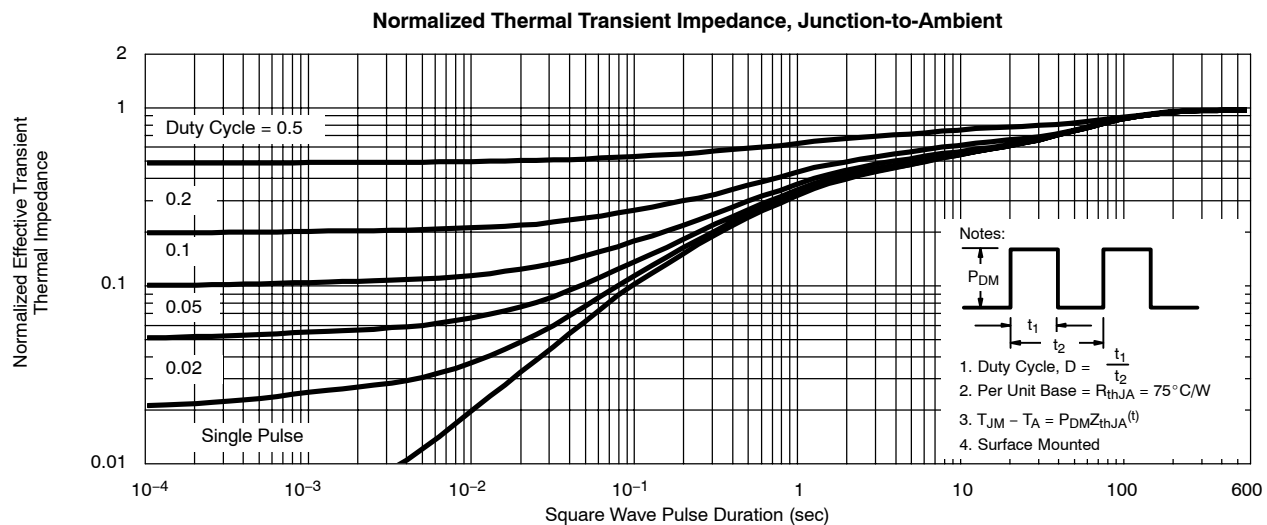
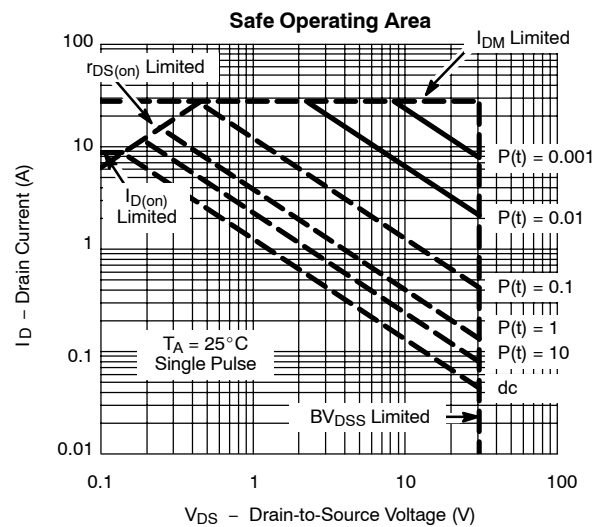
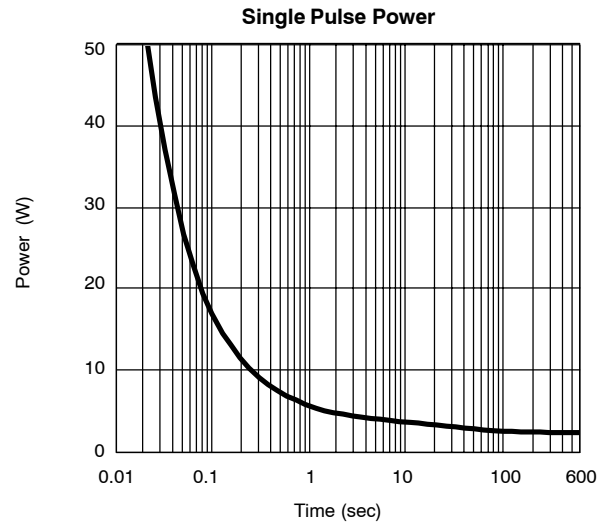
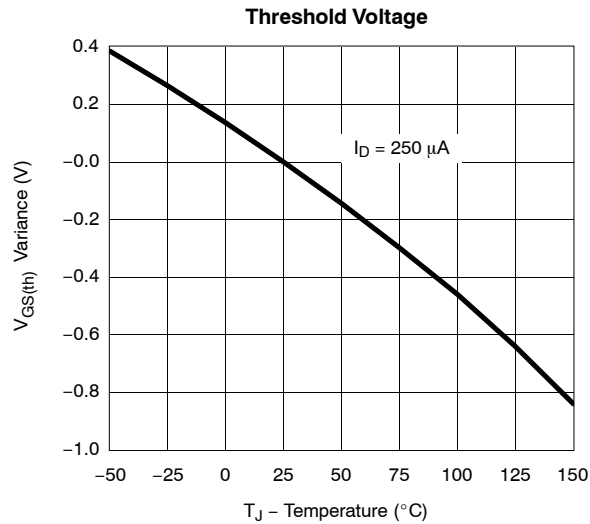
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	1		3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}$, $V_{GS} = \pm 20\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\ \text{V}$, $V_{GS} = 0\ \text{V}$			1	μA
		$V_{DS} = 30\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_J = 85^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}$, $V_{GS} = 10\ \text{V}$	30			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\ \text{V}$, $I_D = 12.2\ \text{A}$		0.0075	0.0095	Ω
		$V_{GS} = 4.5\ \text{V}$, $I_D = 9.4\ \text{A}$		0.013	0.016	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\ \text{V}$, $I_D = 12.2\ \text{A}$		32		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 1.9\ \text{A}$, $V_{GS} = 0\ \text{V}$		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 15\ \text{V}$, $V_{GS} = 4.5\ \text{V}$, $I_D = 12.2\ \text{A}$		13.5	21	nC
Gate-Source Charge	Q_{gs}			7.1		
Gate-Drain Charge	Q_{gd}			4.7		
Gate Resistance	R_g	$f = 1\ \text{MHz}$	0.5	1.0	1.7	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\ \text{V}$, $R_L = 15\ \Omega$ $I_D \cong 1\ \text{A}$, $V_{GEN} = 10\ \text{V}$, $R_G = 6\ \Omega$		10	15	ns
Rise Time	t_r			10	15	
Turn-Off Delay Time	$t_{d(off)}$			40	60	
Fall Time	t_f			12	20	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1.9\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$		45	70	

Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)****On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature****Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage**

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



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